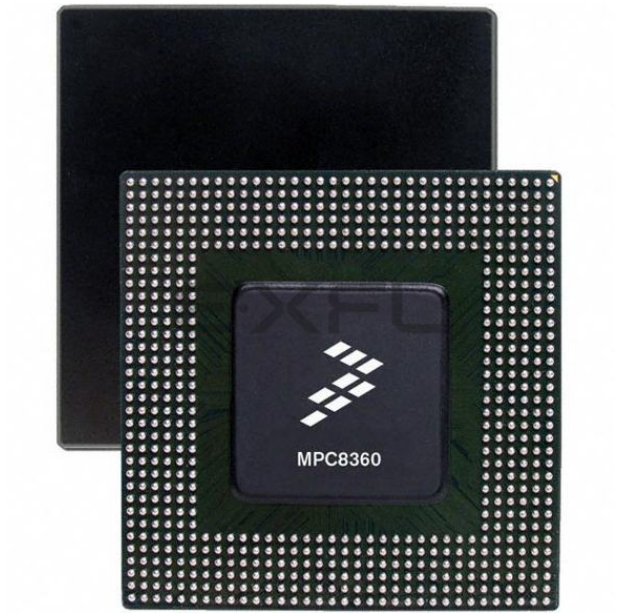

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	740-LBGA
Supplier Device Package	740-TBGA (37.5x37.5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8360eczuagdg

- Eight TDM interfaces on the MPC8360E and four TDM interfaces on the MPC8358E with 1-bit mode for E3/T3 rates in clear channel
- Sixteen independent baud rate generators and 30 input clock pins for supplying clocks to UCC and MCC serial channels (MCC is only available on the MPC8360E)
- Four independent 16-bit timers that can be interconnected as four 32-bit timers
- Interworking functionality:
  - Layer 2 10/100-Base T Ethernet switch
  - ATM-to-ATM switching (AAL0, 2, 5)
  - Ethernet-to-ATM switching with L3/L4 support
  - PPP interworking

- Security engine is optimized to handle all the algorithms associated with IPSec, SSL/TLS, SRTP, 802.11i®, iSCSI, and IKE processing. The security engine contains four crypto-channels, a controller, and a set of crypto execution units (EUs).
  - Public key execution unit (PKEU) supporting the following:
    - RSA and Diffie-Hellman
    - Programmable field size up to 2048 bits
    - Elliptic curve cryptography
    - F2m and F(p) modes
    - Programmable field size up to 511 bits
  - Data encryption standard execution unit (DEU)
    - DES, 3DES
    - Two key (K1, K2) or three key (K1, K2, K3)
    - ECB and CBC modes for both DES and 3DES
  - Advanced encryption standard unit (AESU)
  - Implements the Rinjdael symmetric key cipher
  - Key lengths of 128, 192, and 256 bits, two key
    - ECB, CBC, CCM, and counter modes
  - ARC four execution unit (AFEU)
    - Implements a stream cipher compatible with the RC4 algorithm
    - 40- to 128-bit programmable key
  - Message digest execution unit (MDEU)
    - SHA with 160-, 224-, or 256-bit message digest
    - MD5 with 128-bit message digest
    - HMAC with either SHA or MD5 algorithm
  - Random number generator (RNG)
  - Four crypto-channels, each supporting multi-command descriptor chains
    - Static and/or dynamic assignment of crypto-execution units via an integrated controller
    - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes
  - Storage/NAS XOR parity generation accelerator for RAID applications
- Dual DDR SDRAM memory controllers on the MPC8360E and a single DDR SDRAM memory controller on the MPC8358E
  - Programmable timing supporting both DDR1 and DDR2 SDRAM
  - On the MPC8360E, the DDR buses can be configured as two 32-bit buses or one 64-bit bus; on the MPC8358E, the DDR bus can be configured as a 32- or 64-bit bus
  - 32- or 64-bit data interface, up to 333 MHz (for the MPC8360E) and 266 MHz (for the MPC8358E) data rate
  - Four banks of memory, each up to 1 Gbyte

This figure shows the undershoot and overshoot voltage of the PCI interface of the device for the 3.3-V signals, respectively.

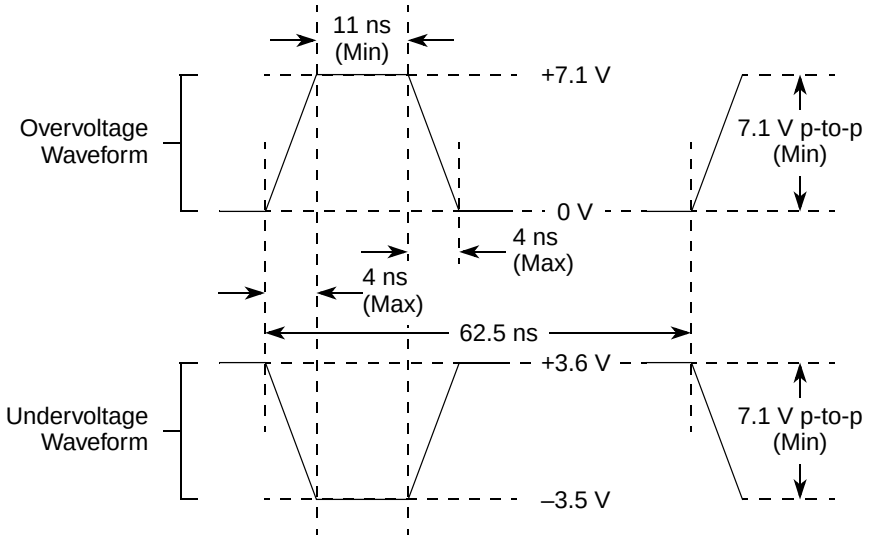


Figure 4. Maximum AC Waveforms on PCI interface for 3.3-V Signaling

2.1.3 Output Driver Characteristics

This table provides information on the characteristics of the output driver strengths. The values are preliminary estimates.

Table 3. Output Drive Capability

Driver Type	Output Impedance (Ω)	Supply Voltage
Local bus interface utilities signals	42	OV_{DD} = 3.3 V
PCI signals	25	
PCI output clocks (including PCI_SYNC_OUT)	42	
DDR signal	20 36 (half-strength mode)[1]	GV_{DD} = 2.5 V
DDR2 signal	18 36 (half-strength mode)[1]	GV_{DD} = 1.8 V
10/100/1000 Ethernet signals	42	LV_{DD} = 2.5/3.3 V
DUART, system control, I^2C, SPI, JTAG	42	OV_{DD} = 3.3 V
GPIO signals	42	OV_{DD} = 3.3 V LV_{DD} = 2.5/3.3 V

Note:
1. DDR output impedance values for half strength mode are verified by design and not tested.

2.2 Power Sequencing

This section details the power sequencing considerations for the MPC8360E/58E.

2.2.1 Power-Up Sequencing

MPC8360E/58E does not require the core supply voltage (V_{DD} and AV_{DD}) and I/O supply voltages (GV_{DD}, LV_{DD}, and OV_{DD}) to be applied in any particular order. During the power ramp up, before the power supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins are actively be driven and cause contention and excessive current from 3A to 5A. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD}, LV_{DD}, and OV_{DD}) and assert $\overline{\text{PORESET}}$ before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V, see this figure.

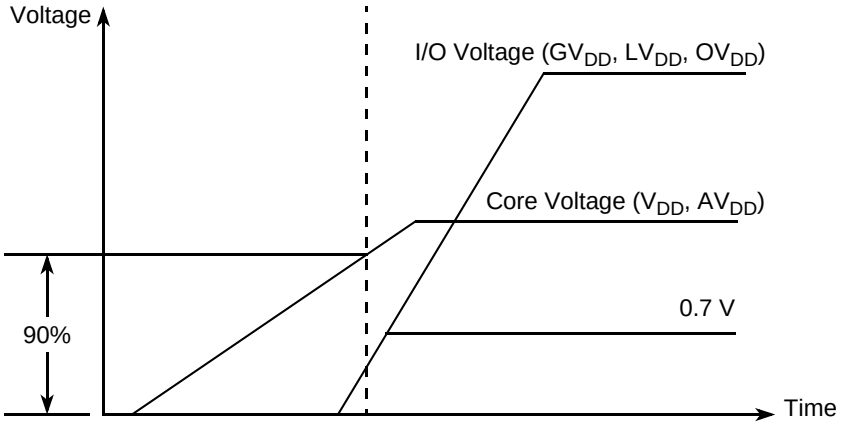


Figure 5. Power Sequencing Example

I/O voltage supplies (GV_{DD}, LV_{DD}, and OV_{DD}) do not have any ordering requirements with respect to one another.

2.2.2 Power-Down Sequencing

The MPC8360E/58E does not require the core supply voltage and I/O supply voltages to be powered down in any particular order.

3 Power Characteristics

The estimated typical power dissipation values are shown in these tables.

Table 4. MPC8360E TBGA Core Power Dissipation[1]

Core Frequency (MHz)	CSB Frequency (MHz)	QUICC Engine Frequency (MHz)	Typical	Maximum	Unit	Notes
266	266	500	5.0	5.6	W	2, 3, 5
400	266	400	4.5	5.0	W	2, 3, 4
533	266	400	4.8	5.3	W	2, 3, 4
667	333	400	5.8	6.3	W	3, 6, 7, 8
500	333	500	5.9	6.4	W	3, 6, 7, 8

6.1 DDR and DDR2 SDRAM DC Electrical Characteristics

This table provides the recommended operating conditions for the DDR2 SDRAM component(s) of the device when GV_{DD}(typ) = 1.8 V.

Table 14. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	1.71	1.89	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.125	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.125	V	—
Output leakage current	I_{OZ}	—	±10	µA	4
Output high current (V_{OUT} = 1.420 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	±10	µA	—
Input current (0 V ≤ V_{IN} ≤ GV_{DD})	I_{IN}	—	±10	µA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to equal 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} cannot exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to equal MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

This table provides the DDR2 capacitance when GV_{DD}(typ) = 1.8 V.

Table 15. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the recommended operating conditions for the DDR SDRAM component(s) of the device when GV_{DD}(typ) = 2.5 V.

Table 16. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3

Table 16. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input high voltage	V_{IH}	MV_{REF} + 0.18	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.18	V	—
Output leakage current	I_{OZ}	—	±10	µA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–15.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	15.2	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	±10	µA	—
Input current (0 V ≤V_{IN} ≤OV_{DD})	I_{IN}	—	±10	µA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤V_{OUT} ≤GV_{DD}.

This table provides the DDR capacitance when GV_{DD}(typ) = 2.5 V.

Table 17. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25° C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

6.2 DDR and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR and DDR2 SDRAM interface.

6.2.1 DDR and DDR2 SDRAM Input AC Timing Specifications

This table provides the input AC timing specifications for the DDR2 SDRAM interface when GV_{DD}(typ) = 1.8 V.

Table 18. DDR2 SDRAM Input AC Timing Specifications for GV_{DD}(typ) = 1.8 V

At recommended operating conditions with GV_{DD} of 1.8 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V	—

This figure provides the AC test load for the DDR bus.

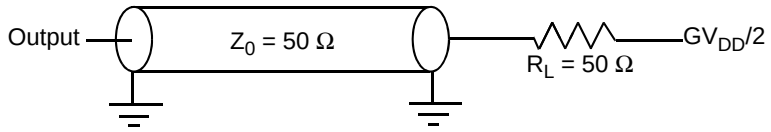


Figure 8. DDR AC Test Load

Table 22. DDR and DDR2 SDRAM Measurement Conditions

Symbol	DDR	DDR2	Unit	Notes
V_{TH}	MV_{REF} ± 0.31 V	MV_{REF} ± 0.25 V	V	1
V_{OUT}	0.5 × GV_{DD}	0.5 × GV_{DD}	V	2

Notes:
1. Data input threshold measurement point.
2. Data output measurement point.

This figure shows the DDR SDRAM output timing diagram for source synchronous mode.

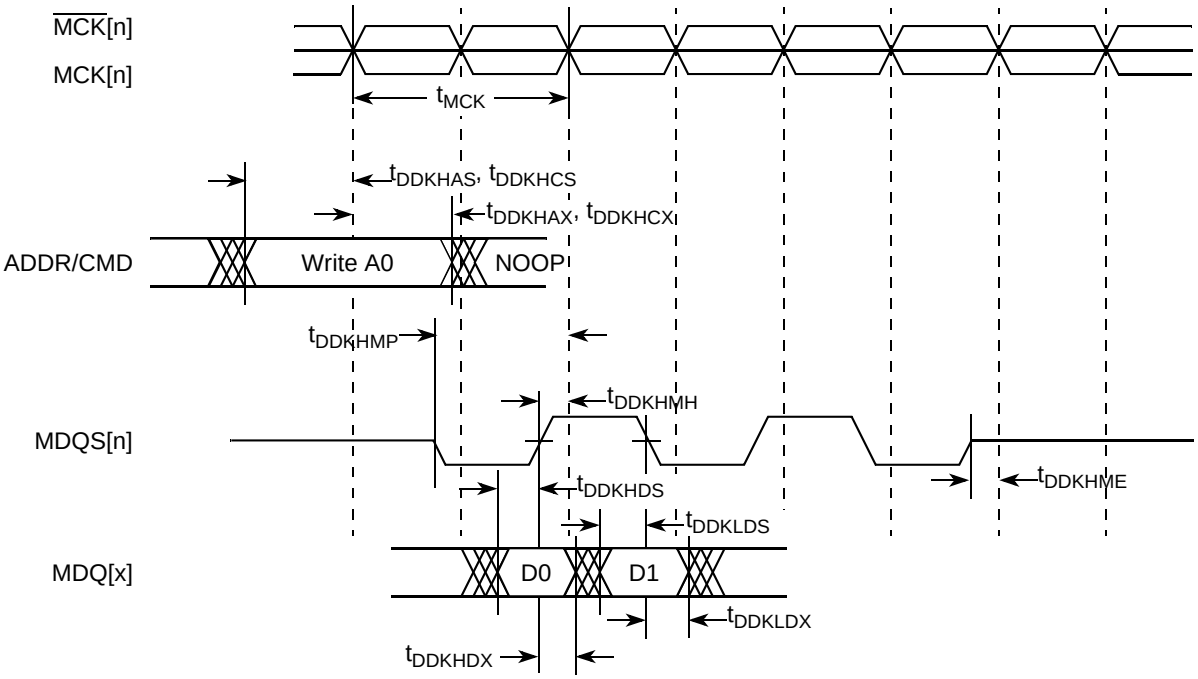


Figure 9. DDR SDRAM Output Timing Diagram for Source Synchronous Mode

8.2.2 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.2.1 MII Transmit AC Timing Specifications

This table provides the MII transmit AC timing specifications.

Table 29. MII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX} t_{MTKHDV}	1 —	5	— 15	ns
TX_CLK data clock rise time, (20% to 80%)	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall time, (80% to 20%)	t_{MTXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure shows the MII transmit AC timing diagram.

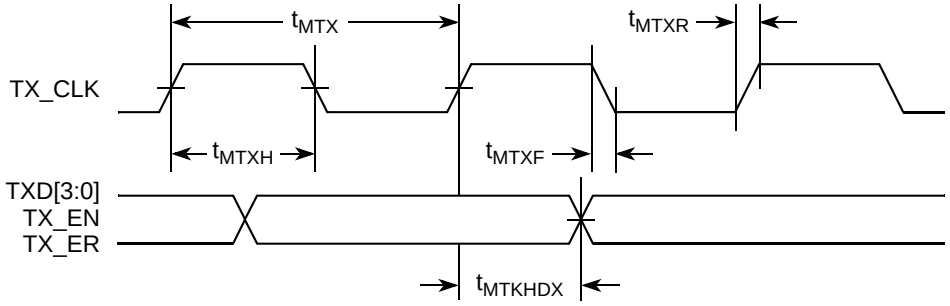


Figure 12. MII Transmit AC Timing Diagram

8.2.4.2 TBI Receive AC Timing Specifications

This table provides the TBI receive AC timing specifications.

Table 34. TBI Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
PMA_RX_CLK clock period	t_{TRX}	—	16.0	—	ns	—
PMA_RX_CLK skew	t_{SKTRX}	7.5	—	8.5	ns	—
RX_CLK duty cycle	t_{TRXH}/t_{TRX}	40	—	60	%	—
RCG[9:0] setup time to rising PMA_RX_CLK	t_{TRDVKH}	2.5	—	—	ns	2
RCG[9:0] hold time to rising PMA_RX_CLK	t_{TRDXKH}	1.0	—	—	ns	2
RX_CLK clock rise time, V_{IL}(min) to V_{IH}(max)	t_{TRXR}	0.7	—	2.4	ns	—
RX_CLK clock fall time, V_{IH}(max) to V_{IL}(min)	t_{TRXF}	0.7	—	2.4	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{TRDVKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{TRX} clock reference (K) going to the high (H) state or setup time. Also, t_{TRDXKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the t_{TRX} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{TRX} represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (TRX).
2. Setup and hold time of even numbered RCG are measured from riding edge of PMA_RX_CLK1. Setup and hold time of odd numbered RCG are measured from riding edge of PMA_RX_CLK0.

This figure shows the TBI receive AC timing diagram.

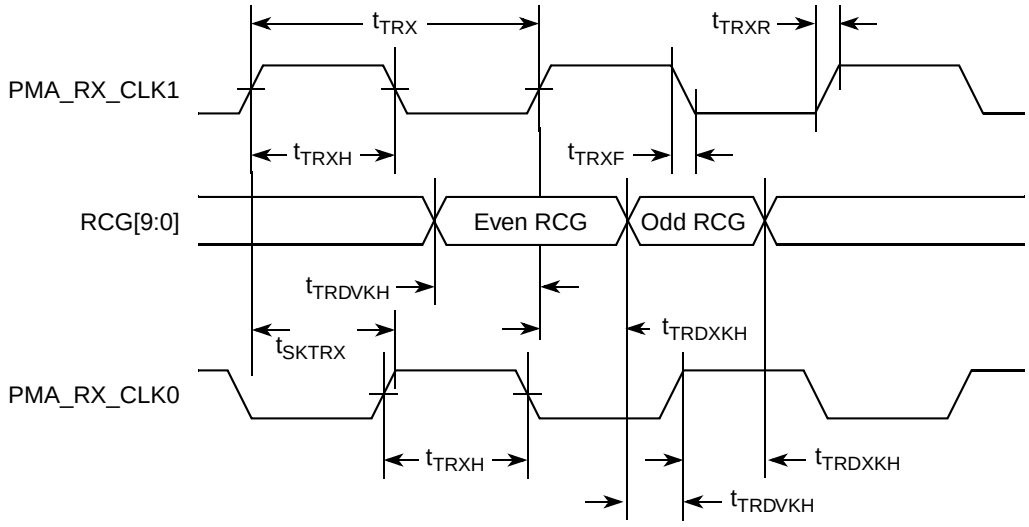


Figure 19. TBI Receive AC Timing Diagram

Table 41. Local Bus General Timing Parameters—DLL Bypass Mode[9] (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus clock to output valid	t_{LBKHOV}	—	3	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4	ns	8

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to falling edge of LCLK0 (for all outputs and for $\overline{\text{LGTA}}$ and LUPWAIT inputs) or rising edge of LCLK0 (for all other inputs).
3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is not set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is set and when the load on LALE output pin equals to the load on LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
9. DLL bypass mode is not recommended for use at frequencies above 66 MHz.

This figure provides the AC test load for the local bus.

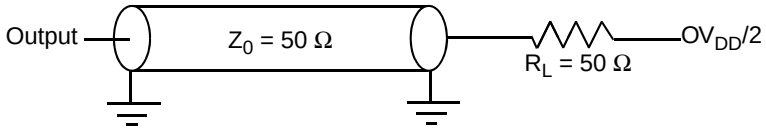


Figure 22. Local Bus C Test Load

These figures show the local bus signals.

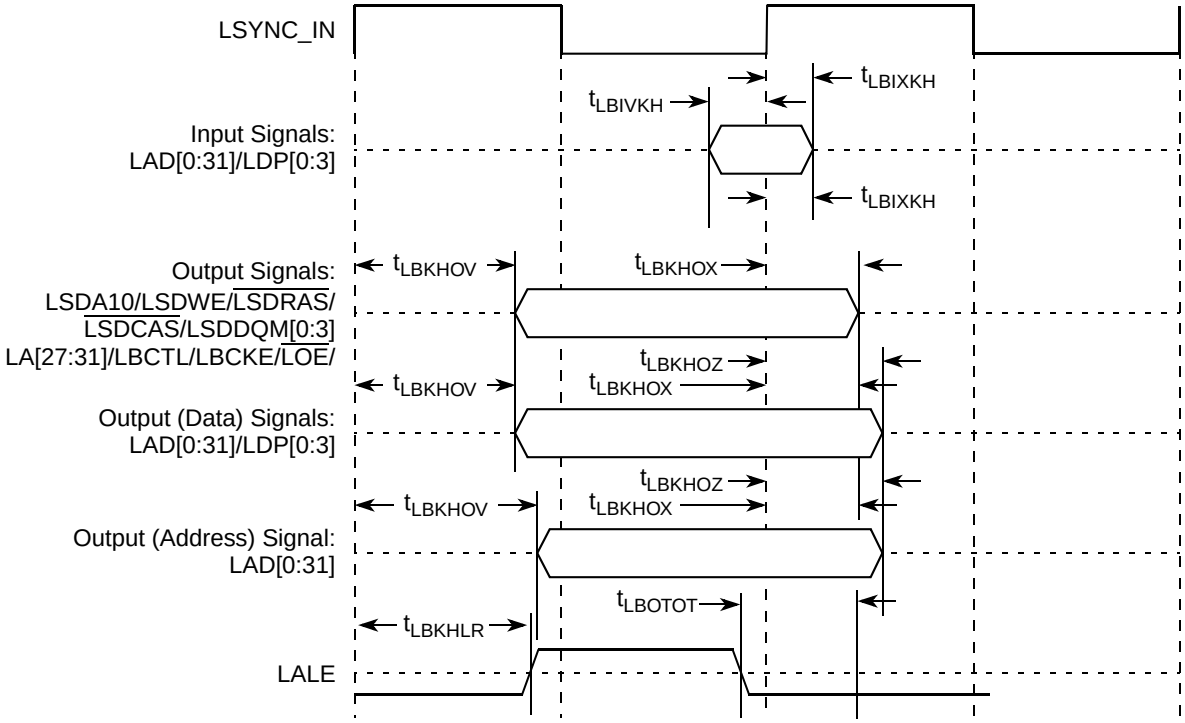


Figure 23. Local Bus Signals, Nonspecial Signals Only (DLL Enabled)

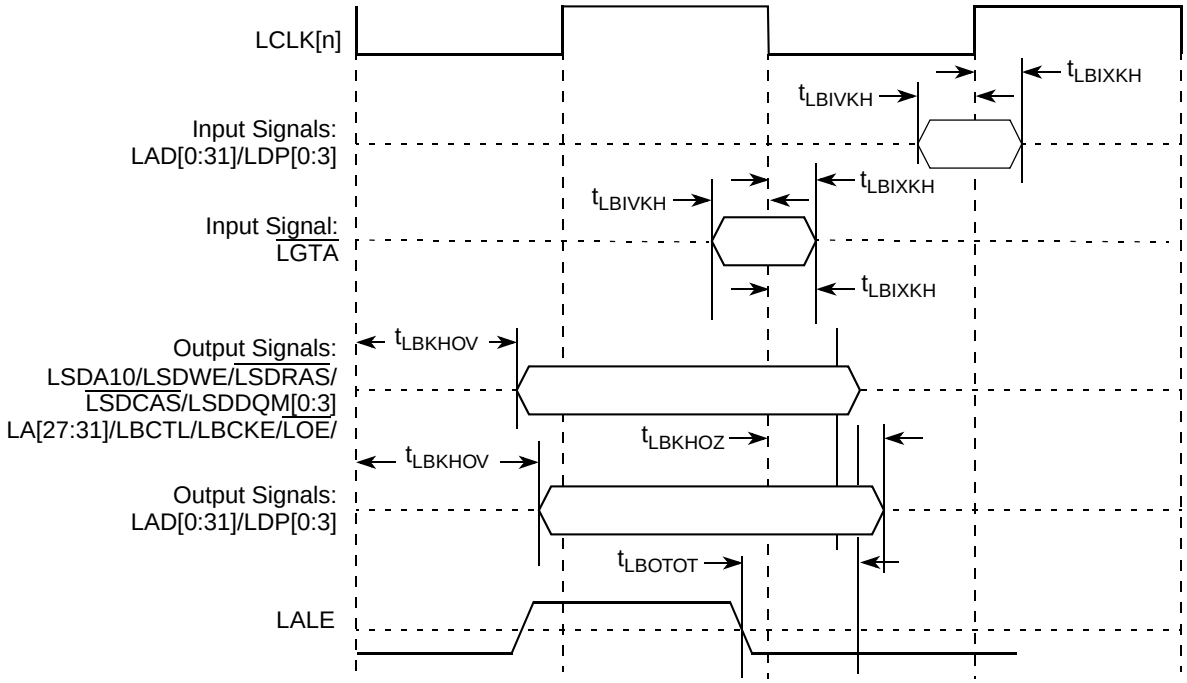


Figure 24. Local Bus Signals, Nonspecial Signals Only (DLL Bypass Mode)

This figure provides the AC test load for the I^2C.

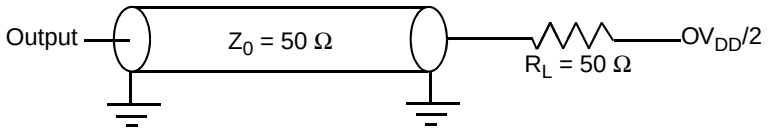


Figure 34. I^2C AC Test Load

This figure shows the AC timing diagram for the I^2C bus.

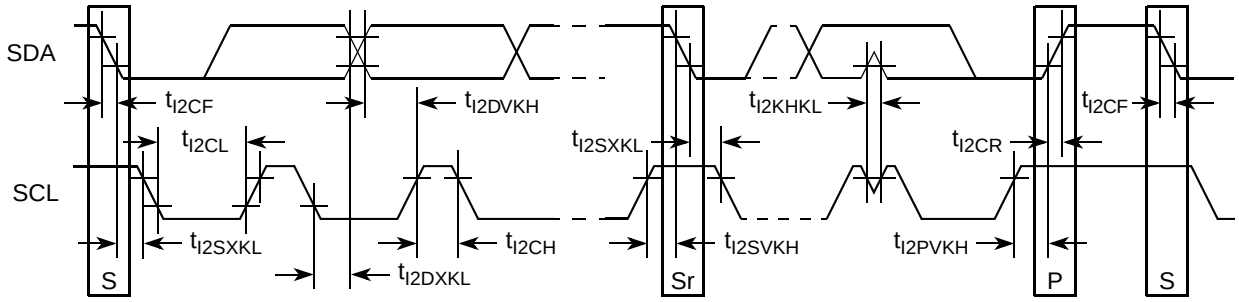


Figure 35. I^2C Bus AC Timing Diagram

12 PCI

This section describes the DC and AC electrical specifications for the PCI bus of the MPC8360E/58E.

12.1 PCI DC Electrical Characteristics

This table provides the DC electrical characteristics for the PCI interface of the device.

Table 46. PCI DC Electrical Characteristics

Parameter	Symbol	Test Condition	Min	Max	Unit
High-level input voltage	V_{IH}	$V_{OUT} \geq V_{OH}$ (min) or	$0.5 \times OV_{DD}$	$OV_{DD} + 0.5$	V
Low-level input voltage	V_{IL}	$V_{OUT} \leq V_{OL}$ (max)	-0.5	$0.3 \times OV_{DD}$	V
High-level output voltage	V_{OH}	I_{OH} = –500 µA	$0.9 \times OV_{DD}$	—	V
Low-level output voltage	V_{OL}	I_{OL} = 1500 µA	—	$0.1 \times OV_{DD}$	V
Input current	I_{IN}	$0 V \leq V_{IN}$[1] $\leq OV_{DD}$	—	±10	µA

12.2 PCI AC Electrical Specifications

This section describes the general AC timing parameters of the PCI bus of the device. Note that the PCI_CLK or PCI_SYNC_IN signal is used as the PCI input clock depending on whether the device is configured as a host or agent device. This table provides the PCI AC timing specifications at 66 MHz.

Table 47. PCI AC Timing Specifications at 66 MHz

Parameter	Symbol[1]	Min	Max	Unit	Notes
Clock to output valid	t_{PCKHOV}	—	6.0	ns	2, 5
Output hold from clock	t_{PCKHOX}	1	—	ns	2

14.2 GPIO AC Timing Specifications

This table provides the GPIO input and output AC timing specifications.

Table 52. GPIO Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Typ	Unit
GPIO inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation.

This figure provides the AC test load for the GPIO.

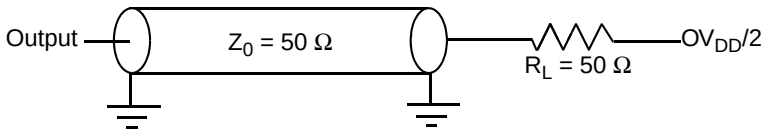


Figure 40. GPIO AC Test Load

15 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins of the MPC8360E/58E.

15.1 IPIC DC Electrical Characteristics

This table provides the DC electrical characteristics for the external interrupt pins of the IPIC.

Table 53. IPIC DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±10	μA
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Notes:
1. This table applies for pins $\overline{\text{IRQ}}$[0:7], $\overline{\text{IRQ\_OUT}}$, $\overline{\text{MCP\_OUT}}$, and CE ports Interrupts.
2. $\overline{\text{IRQ\_OUT}}$ and $\overline{\text{MCP\_OUT}}$ are open drain pins, thus V_{OH} is not relevant for those pins.

17 TDM/SI

This section describes the DC and AC electrical specifications for the time-division-multiplexed and serial interface of the MPC8360E/58E.

17.1 TDM/SI DC Electrical Characteristics

This table provides the DC electrical characteristics for the device TDM/SI.

Table 57. TDM/SI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –2.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤V_{IN} ≤OV_{DD}	—	±10	μA

17.2 TDM/SI AC Timing Specifications

This table provides the TDM/SI input and output AC timing specifications.

Table 58. TDM/SI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max[3]	Unit
TDM/SI outputs—External clock delay	t_{SEKHOV}	2	10	ns
TDM/SI outputs—External clock high impedance	t_{SEKHOX}	2	10	ns
TDM/SI inputs—External clock input setup time	t_{SEIVKH}	5	—	ns
TDM/SI inputs—External clock input hold time	t_{SEIXKH}	2	—	ns

Notes:

1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{SEKHOX} symbolizes the TDM/SI outputs external timing (SE) for the time $t_{TDM/SI}$ memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).
3. Timings are measured from the positive or negative edge of the clock, according to SIxMR [CE] and SITXCEI[TXCEIx]. Refer *MPC8360E Integrated Communications Processor Reference Manual* for more details.

This figure provides the AC test load for the TDM/SI.

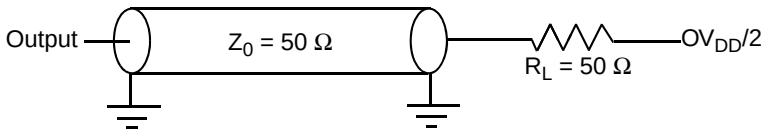
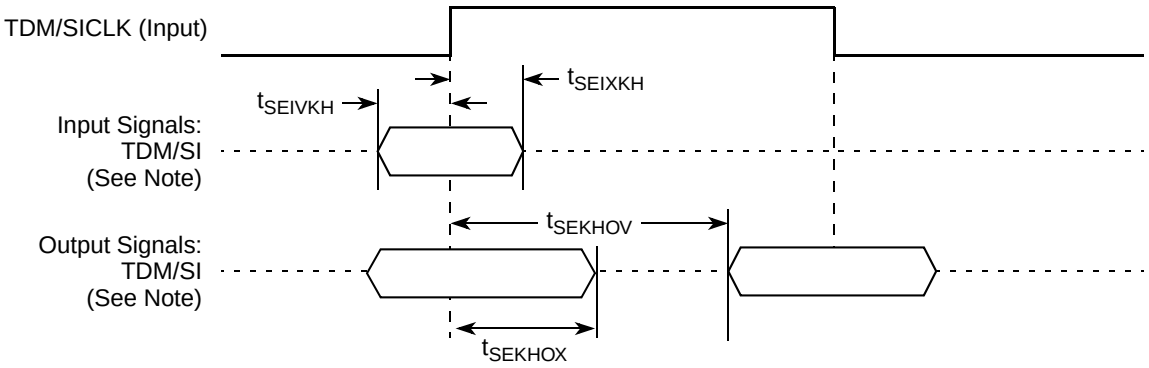


Figure 44. TDM/SI AC Test Load

Figure 45 represents the AC timing from Table 56. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

This figure shows the TDM/SI timing with external clock.



Note: The clock edge is selectable on TDM/SI

Figure 45. TDM/SI AC Timing (External Clock) Diagram

17.3 UTOPIA/POS

This section describes the DC and AC electrical specifications for the UTOPIA/POS of the MPC8360E/58E.

17.4 UTOPIA/POS DC Electrical Characteristics

This table provides the DC electrical characteristics for the device UTOPIA.

Table 59. UTOPIA DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤V_{IN} ≤OV_{DD}	—	±10	μA

17.5 UTOPIA/POS AC Timing Specifications

This table provides the UTOPIA input and output AC timing specifications.

Table 60. UTOPIA AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit	Notes
UTOPIA outputs—Internal clock delay	t_{UIKHOV}	0	11.5	ns	—
UTOPIA outputs—External clock delay	t_{UEKHOV}	1	11.6	ns	—
UTOPIA outputs—Internal clock high impedance	t_{UIKHOX}	0	8.0	ns	—
UTOPIA outputs—External clock high impedance	t_{UEKHOX}	1	10.0	ns	—
UTOPIA inputs—Internal clock input setup time	t_{UIIVKH}	6	—	ns	—
UTOPIA inputs—External clock input setup time	t_{UEIVKH}	4	—	ns	3

19 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8360E/58E.

19.1 USB DC Electrical Characteristics

This table provides the DC electrical characteristics for the USB interface.

Table 64. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 µA	V_{OH}	OV_{DD} – 0.4	—	V
Low-level output voltage, I_{OL} = 100 µA	V_{OL}	—	0.2	V
Input current	I_{IN}	—	±10	µA

19.2 USB AC Electrical Specifications

This table describes the general timing parameters of the USB interface of the device.

Table 65. USB General Timing Parameters

Parameter	Symbol[1]	Min	Max	Unit	Notes	Note
USB clock cycle time	t_{USCK}	20.83	—	ns	Full speed 48 MHz	—
USB clock cycle time	t_{USCK}	166.67	—	ns	Low speed 6 MHz	—
Skew between TXP and TXN	t_{USTSPN}	—	5	ns	—	2
Skew among RXP, RXN, and RXD	$t_{USRSPND}$	—	10	ns	Full speed transitions	2
Skew among RXP, RXN, and RXD	t_{USRPND}	—	100	ns	Low speed transitions	2

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(state)(signal)}}$ for receive signals and $t_{\text{(first two letters of functional block)(state)(signal)}}$ for transmit signals. For example, $t_{USRSPND}$ symbolizes USB timing (US) for the USB receive signals skew (RS) among RXP, RXN, and RXD (PND). Also, t_{USTSPN} symbolizes USB timing (US) for the USB transmit signals skew (TS) between TXP and TXN (PN).
2. Skew measurements are done at $OV_{DD}/2$ of the rising or falling edge of the signals.

This figure provide the AC test load for the USB.

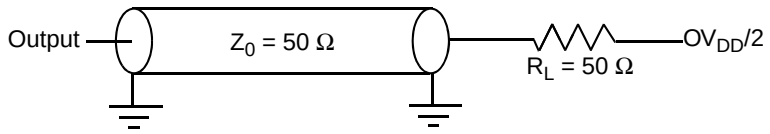


Figure 52. USB AC Test Load

20.3 Pinout Listings

Refer to AN3097, “MPC8360/MPC8358E PowerQUICC Design Checklist,” for proper pin termination and usage.

This table shows the pin list of the MPC8360E TBGA package.

Table 66. MPC8360E TBGA Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Primary DDR SDRAM Memory Controller Interface				
MEMC1_MDQ[0:31]	AJ34, AK33, AL33, AL35, AJ33, AK34, AK32, AM36, AN37, AN35, AR34, AT34, AP37, AP36, AR36, AT35, AP34, AR32, AP32, AM31, AN33, AM34, AM33, AM30, AP31, AM27, AR30, AT32, AN29, AP29, AN27, AR29	I/O	GV_{DD}	—
MEMC1_MDQ[32:63]/ MEMC2_MDQ[0:31]	AN8, AN7, AM8, AM6, AP9, AN9, AT7, AP7, AU6, AP6, AR4, AR3, AT6, AT5, AR5, AT3, AP4, AM5, AP3, AN3, AN5, AL5, AN4, AM2, AL2, AH5, AK3, AJ2, AJ3, AH4, AK4, AH3	I/O	GV_{DD}	—
MEMC1_MECC[0:4]/ MSRCID[0:4]	AP24, AN22, AM19, AN19, AM24	I/O	GV_{DD}	—
MEMC1_MECC[5]/ MDVAL	AM23	I/O	GV_{DD}	—
MEMC1_MECC[6:7]	AM22, AN18	I/O	GV_{DD}	—
MEMC1_MDM[0:3]	AL36, AN34, AP33, AN28	O	GV_{DD}	—
MEMC1_MDM[4:7]/ MEMC2_MDM[0:3]	AT9, AU4, AM3, AJ6	O	GV_{DD}	—
MEMC1_MDM[8]	AP27	O	GV_{DD}	—
MEMC1_MDQS[0:3]	AK35, AP35, AN31, AM26	I/O	GV_{DD}	—
MEMC1_MDQS[4:7]/ MEMC2_MDQS[0:3]	AT8, AU3, AL4, AJ5	I/O	GV_{DD}	—
MEMC1_MDQS[8]	AP26	I/O	GV_{DD}	—
MEMC1_MBA[0:1]	AU29, AU30	O	GV_{DD}	—
MEMC1_MBA[2]	AT30	O	GV_{DD}	—
MEMC1_MA[0:14]	AU21, AP22, AP21, AT21, AU25, AU26, AT23, AR26, AU24, AR23, AR28, AU23, AR22, AU20, AR18	O	GV_{DD}	—
MEMC1_MODT[0:1]	AG33, AJ36	O	GV_{DD}	6
MEMC1_MODT[2:3]/ MEMC2_MODT[0:1]	AT1, AK2	O	GV_{DD}	6
$\overline{\text{MEMC1\_MWE}}$	AT26	O	GV_{DD}	—
$\overline{\text{MEMC1\_MRAS}}$	AT29	O	GV_{DD}	—
$\overline{\text{MEMC1\_MCAS}}$	AT24	O	GV_{DD}	—
$\overline{\text{MEMC1\_MCS}}$[0:1]	AU27, AT27	O	GV_{DD}	—
$\overline{\text{MEMC1\_MCS}}$[2:3]/ $\overline{\text{MEMC2\_MCS}}$[0:1]	AU8, AU7	O	GV_{DD}	—

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI_MODE	D36	I	OV_{DD}	—
M66EN/CE_PF[4]	B37	I/O	OV_{DD}	—
Local Bus Controller Interface				
LAD[0:31]	N32, N33, N35, N36, P37, P32, P34, R36, R35, R34, R33, T37, T35, T34, T33, U37, T32, U36, U34, V36, V35, W37, W35, V33, V32, W34, Y36, W32, AA37, Y33, AA35, AA34	I/O	OV_{DD}	—
LDP[0]/CKSTOP_OUT	AB37	I/O	OV_{DD}	—
LDP[1]/CKSTOP_IN	AB36	I/O	OV_{DD}	—
LDP[2]/LCS[6]	AB35	I/O	OV_{DD}	—
LDP[3]/LCS[7]	AA33	I/O	OV_{DD}	—
LA[27:31]	AC37, AA32, AC36, AC34, AD36	O	OV_{DD}	—
LCS[0:5]	AD33, AG37, AF34, AE33, AD32, AH37	O	OV_{DD}	—
LWE[0:3]/LSDDQM[0:3]/LBS[0:3]	AG35, AG34, AH36, AE32	O	OV_{DD}	—
LBCTL	AD35	O	OV_{DD}	—
LALE	M37	O	OV_{DD}	—
LGPL0/LSDA10/cfg_reset_source0	AB32	I/O	OV_{DD}	—
LGPL1/LSDWE/cfg_reset_source1	AE37	I/O	OV_{DD}	—
LGPL2/LSDRAS/LOE	AC33	O	OV_{DD}	—
LGPL3/LSDCAS/cfg_reset_source2	AD34	I/O	OV_{DD}	—
LGPL4/LGTA/LUPWAIT/LPBSE	AE35	I/O	OV_{DD}	—
LGPL5/cfg_clkin_div	AF36	I/O	OV_{DD}	—
LCKE	G36	O	OV_{DD}	—
LCLK[0]	J33	O	OV_{DD}	—
LCLK[1]/LCS[6]	J34	O	OV_{DD}	—
LCLK[2]/LCS[7]	G37	O	OV_{DD}	—
LSYNC_OUT	F34	O	OV_{DD}	—
LSYNC_IN	G35	I	OV_{DD}	—
Programmable Interrupt Controller				
MCP_OUT	E34	O	OV_{DD}	2
IRQ0/MCP_IN	C37	I	OV_{DD}	—
IRQ[1]/M1SRCID[4]/M2SRCID[4]/ LSRCID[4]	F35	I/O	OV_{DD}	—
IRQ[2]/M1DVAL/M2DVAL/LDVAL	F36	I/O	OV_{DD}	—
IRQ[3]/CORE_SRESET	H34	I/O	OV_{DD}	—

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$\overline{\text{IRQ}}$[4:5]	G33, G32	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[6]/$\overline{\text{LCS}}$[6]/$\overline{\text{CKSTOP\_OUT}}$	E35	I/O	OV_{DD}	—
$\overline{\text{IRQ}}$[7]/$\overline{\text{LCS}}$[7]/$\overline{\text{CKSTOP\_IN}}$	H36	I/O	OV_{DD}	—
DUART				
UART1_SOUT/M1SRCID[0]/ M2SRCID[0]/LSRCID[0]	E32	O	OV_{DD}	—
UART1_SIN/M1SRCID[1]/ M2SRCID[1]/LSRCID[1]	B34	I/O	OV_{DD}	—
$\overline{\text{UART1\_CTS}}$/M1SRCID[2]/ M2SRCID[2]/LSRCID[2]	C34	I/O	OV_{DD}	—
$\overline{\text{UART1\_RTS}}$/M1SRCID[3]/ M2SRCID[3]/LSRCID[3]	A35	O	OV_{DD}	—
I^2C Interface				
IIC1_SDA	D34	I/O	OV_{DD}	2
IIC1_SCL	B35	I/O	OV_{DD}	2
IIC2_SDA	E33	I/O	OV_{DD}	2
IIC2_SCL	C35	I/O	OV_{DD}	2
QUICC Engine				
CE_PA[0]	F8	I/O	LV_{DD0}	—
CE_PA[1:2]	AH1, AG5	I/O	OV_{DD}	—
CE_PA[3:7]	F6, D4, C3, E5, A3	I/O	$LV_{DD}0$	—
CE_PA[8]	AG3	I/O	OV_{DD}	—
CE_PA[9:12]	F7, B3, E6, B4	I/O	$LV_{DD}0$	—
CE_PA[13:14]	AG1, AF6	I/O	OV_{DD}	—
CE_PA[15]	B2	I/O	$LV_{DD}0$	—
CE_PA[16]	AF4	I/O	OV_{DD}	—
CE_PA[17:21]	B16, A16, E17, A17, B17	I/O	$LV_{DD}1$	—
CE_PA[22]	AF3	I/O	OV_{DD}	—
CE_PA[23:26]	C18, D18, E18, A18	I/O	$LV_{DD}1$	—
CE_PA[27:28]	AF2, AE6	I/O	OV_{DD}	—
CE_PA[29]	B19	I/O	$LV_{DD}1$	—
CE_PA[30]	AE5	I/O	OV_{DD}	—
CE_PA[31]	F16	I/O	$LV_{DD}1$	—

ordered, see Section 24.1, "Part Numbers Fully Addressed by this Document," for part ordering details and contact your Freescale sales representative or authorized distributor for more information.

Table 69. Operating Frequencies for the TBGA Package

Characteristic[1]	400 MHz	533 MHz	667 MHz[2]	Unit
e300 core frequency (*core_clk*)	266–400	266–533	266–667	MHz
Coherent system bus frequency (*csb_clk*)	133–333			MHz
QUICC Engine frequency[3] (*ce_clk*)	266–500			MHz
DDR and DDR2 memory bus frequency (MCLK)[4]	100–166.67			MHz
Local bus frequency (LCLK*n*)[5]	16.67–133			MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66.67			MHz
Security core maximum internal operating frequency	133	133	166	MHz

Notes:
1. The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies.
2. The 667 MHz core frequency is based on a 1.3 V V_{DD} supply voltage.
3. The 500 MHz QE frequency is based on a 1.3 V V_{DD} supply voltage.
4. The DDR data rate is 2x the DDR memory bus frequency.
5. The local bus frequency is 1/2, 1/4, or 1/8 of the *lb_clk* frequency (depending on LCRR[CLKDIV]) which is in turn 1× or 2× the *csb_clk* frequency (depending on RCWL[LBCM]).

21.1 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] and RCWL[SVCOD] parameters. This table shows the multiplication factor encodings for the system PLL.

Table 70. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	× 16
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111	× 7
1000	× 8
1001	× 9
1010	× 10
1011	× 11

Table 82. Revision History (continued)

Rev. Number	Date	Substantive Change(s)
3	03/2010	• Changed references to RCWH[PCICKEN] to RCWH[PCICKDRV]. • In Table 2, added extended temperature characteristics. • Added Figure 6, “DDR Input Timing Diagram.” • In Figure 53, “Mechanical Dimensions and Bottom Surface Nomenclature of the TBGA Package,” removed watermark. • Updated the title of Table 19,”DDR SDRAM Input AC Timing Specifications.” • In Table 20, “DDR and DDR2 SDRAM Input AC Timing Specifications Mode,” changed table subtitle. • In Table 27–Table 30, and Table 33—Table 34, changed the rise and fall time specifications to reference 20–80% and 80–20% of the voltage supply, respectively. • In Table 38, “IEEE 1588 Timer AC Specifications,” changed first parameter to “Timer clock frequency.” • In Table 45, “I2C AC Electrical Specifications,” changed units to “ns” for t_{I2DVKH}. • In Table 66, “MPC8360E TBGA Pinout Listing,” and Table 67 “MPC8358E TBGA Pinout Listing, added note 7: “This pin must always be tied to GND” to the TEST pin and added a note to SPARE1 stating: “This pin must always be left not connected.” • In Section 4, “Clock Input Timing,” added note regarding rise/fall time on QUICC Engine block input pins. • Added Section 4.3, “Gigabit Reference Clock Input Timing.” • Updated Section 8.1.1, “10/100/1000 Ethernet DC Electrical Characteristics.” • In Section 20.3, “Pinout Listings,” added sentence stating “Refer to AN3097, ‘MPC8360/MPC8358E PowerQUICC Design Checklist,’ for proper pin termination and usage.” • In Section 21, “Clocking,” removed statement: “The OCCR[PCICDn] parameters select whether CLKIN or CLKIN/2 is driven out on the PCI_CLK_OUTn signals.” • In Section 21.1, “System PLL Configuration,” updated the system VCO frequency conditions. • In Table 80, added extended temperature characteristics.
2	12/2007	Initial release.